

# N-CHANNEL GaAs MES FET NE960R5 SERIES

### 0.5 W X, Ku-BAND POWER GaAs MES FET

#### DESCRIPTION

The NE960R5 Series are 0.5 W GaAs MES FETs designed for middle power transmitter applications for X, Ku-band microwave communication systems. It is capable of delivering 0.5 watt of output power (CW) with high linear gain, high efficiency and low distortion and are suitable as driver amplifiers for our X, Ku-band amplifiers etc. The NE960R500 is available in chip form. The NE960R500 has a via hole source grounding and PHS (Plated Heat Sink) for superior RF performance. The NE960R575 is available in a hermetically sealed ceramic package. Reliability and performance uniformity are assured by NEC's stringent quality and control procedures.

#### FEATURES

- High Output Power :  $P_o (1 \text{ dB}) = +27.5 \text{ dBm TYP.}$
- High Linear Gain :  $9.0 \text{ dB TYP.}$
- High Power Added Efficiency:  $30 \% \text{ TYP. @ } V_{DS} = 9 \text{ V, } I_{Dset} = 180 \text{ mA, } f = 14.5 \text{ GHz}$

#### ORDERING INFORMATION

Part Number	Package	Supplying Form
NE960R500	00 (CHIP)	ESD protective envelope
NE960R575	75	

**Remark** To order evaluation samples, please contact your nearby sales office.

Part number for sample order: NE960R500, NE960R575

**Caution** Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.  
Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = +25°C)**

Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V <sub>DS</sub>	15	V
★ Gate to Source Voltage	V <sub>GSO</sub>	-7	V
Drain Current	I <sub>D</sub>	0.7	A
Gate Forward Current	I <sub>GF</sub>	+5.0	mA
Gate Reverse Current	I <sub>GR</sub>	-5.0	mA
★ Total Power Dissipation	P <sub>T</sub>	5.0	W
Channel Temperature	T <sub>ch</sub>	175	°C
Storage Temperature	T <sub>stg</sub>	-65 to +175	°C

**RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V <sub>DS</sub>		-	9.0	9.0	V
Gain Compression	G <sub>comp</sub>		-	-	3.0	dB
Channel Temperature	T <sub>ch</sub>		-	-	+130	°C

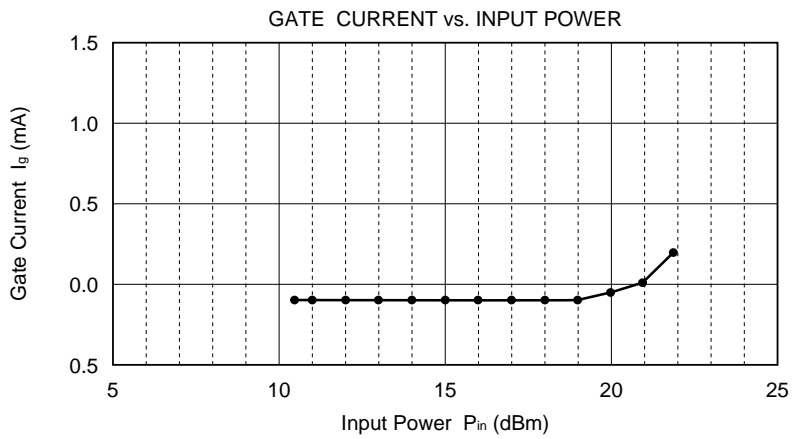
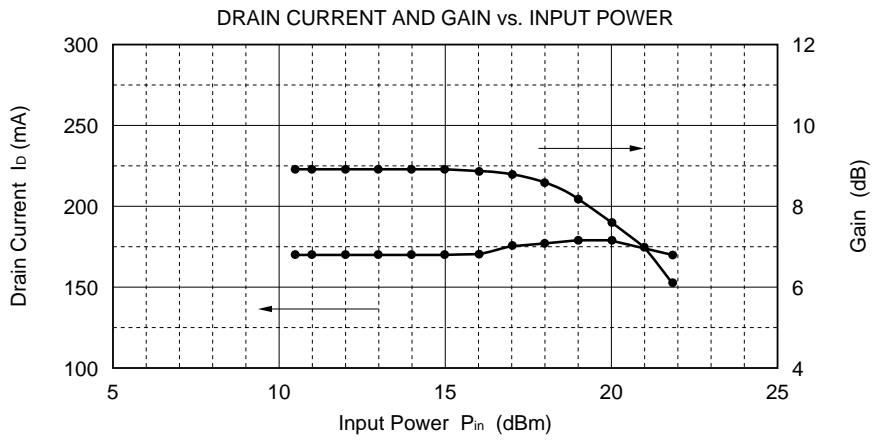
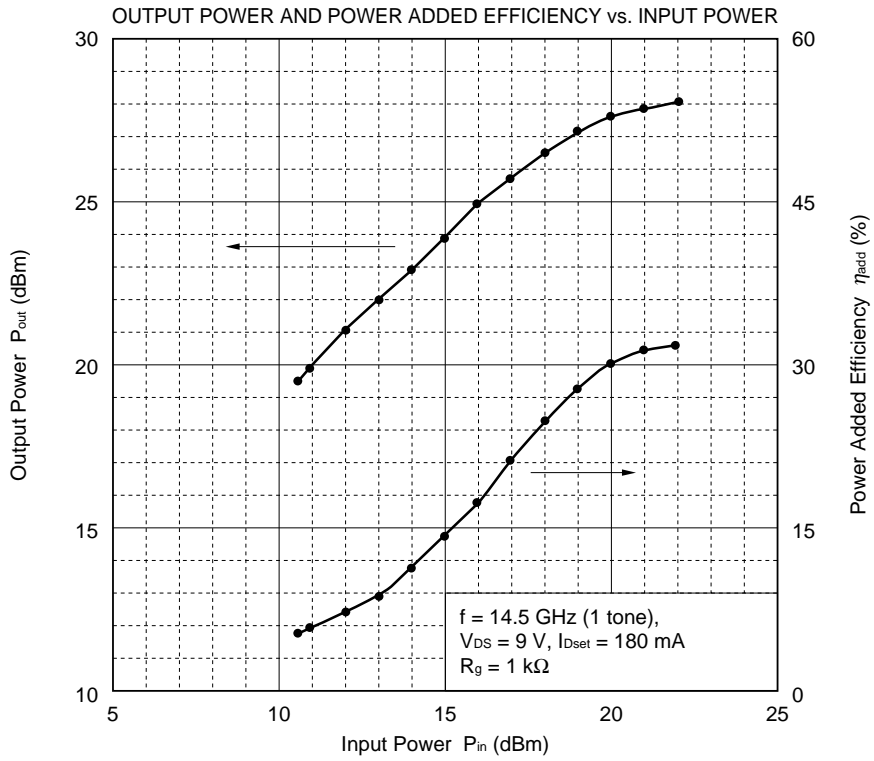
**ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = +25°C, unless otherwise specified, using NEC standard test fixture.)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Saturated Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 1.5 V, V <sub>GS</sub> = 0 V	0.18	0.4	0.7	A
Pinch-off Voltage	V <sub>p</sub>	V <sub>DS</sub> = 2.5 V, I <sub>D</sub> = 2 mA	-2.5	-1.8	-0.5	V
Gate to Drain Break Down Voltage	BV <sub>gd</sub>	I <sub>gd</sub> = 2 mA	15	-	-	V
★ Thermal Resistance	R <sub>th</sub>	Channel to Case	-	-	30	°C/W
Output Power at P <sub>in</sub> = +19 dBm	P <sub>out</sub>	f = 14.5 GHz, V <sub>DS</sub> = 9.0 V	25.5	26.5	-	dBm
Output Power at 1 dB Gain Compression Point	P <sub>o(1dB)</sub>	R <sub>g</sub> = 1 kΩ I <sub>Dset</sub> = 180 mA (RF OFF)	-	27.5	-	dBm
Power Added Efficiency at P <sub>o(1dB)</sub>	η <sub>add</sub>		-	30	-	%
Linear Gain	G <sub>L</sub>		8.0	9.0	-	dB

**Remark** DC and RF performance is 100 % testing.

TYPICAL CHARACTERISTICS (T<sub>A</sub> = +25°C)



**Remark** The graphs indicate nominal characteristics.

**S-PARAMETERS**

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

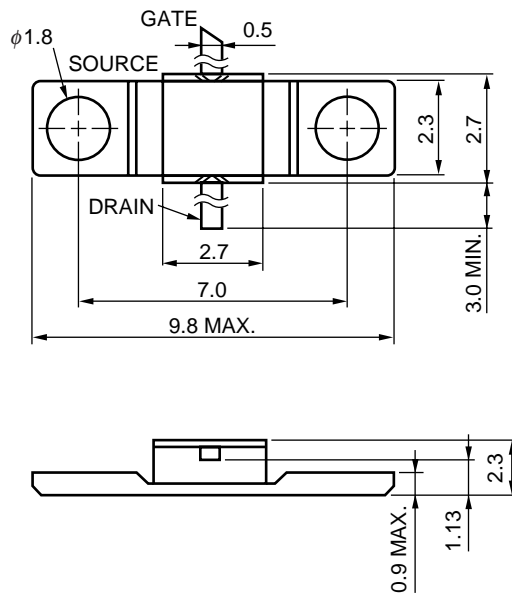
Click here to download S-parameters.

[RF and Microwave] → [Device Parameters]

URL <http://www.ncsd.necel.com/>

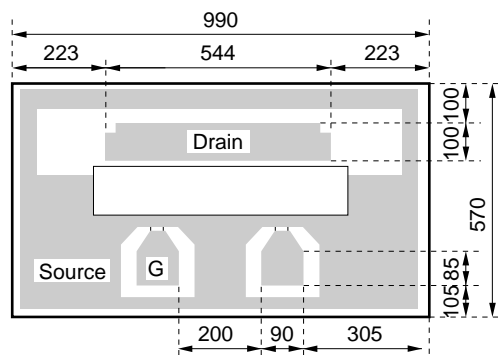
PACKAGE DIMENSIONS

PACKAGE CODE-75 (Unit: mm)



★ PHYSICAL DIMENSIONS

NE960R500 (CHIP) (Unit:  $\mu\text{m}$ )



**Remark** Chip thickness: 100  $\mu\text{m}$   
 G : Gate

★ **RECOMMENDED SOLDERING CONDITIONS**

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Partial Heating	Peak temperature (pin temperature) : 350°C or below Soldering time (per pin of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2 % (Wt.) or below	HS350-P3

**Caution Do not use different soldering methods together (except for partial heating).**

**CHIP HANDLING**

**DIE ATTACHMENT**

Die attach can be accomplished with a Au-Sn (300 ±10°C) performs in a forming gas environment. Epoxy die attach is not recommended.

**BONDING**

Gate and drain bonding wires should be minimum length, semi-hard gold wire (3 to 8 % elongation) 30 microns or less in diameter.

Bonding should be performed with a wedge tip that has a taper of approximately 15 %.

Die attach and bonding time should be kept to a minimum. As a general rule, the bonding operation should be kept within a 280°C\_5 minute curve. If longer periods are required, the temperature should be lowered.

**PRECAUTIONS**

The user must operate in a clean, dry environment.

The chip channel is glassivated for mechanical protection only and does not preclude the necessity of a clean environment.

The bonding equipment should be periodically checked for sources of surge voltage and should be properly grounded at all times. In fact, all test and handling equipment should be grounded to minimize the possibilities of static discharge.

- **The information in this document is current as of August, 2003. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.**
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M8E 00.4-0110

<p><b>Caution</b></p>	<p>GaAs Products</p>	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"> <li>• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.               <ol style="list-style-type: none"> <li>1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.</li> <li>2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.</li> </ol> </li> <li>• Do not burn, destroy, cut, crush, or chemically dissolve the product.</li> <li>• Do not lick the product or in any way allow it to enter the mouth.</li> </ul>
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► For further information, please contact

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